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Emerging Challenges in NAND Flash Technology

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Presentation Agenda

- ◆ NAND Flash Market Overview
- ◆ Technology Scaling Trend & Forecast
- ◆ Technology Scaling Limitation & Hurdle
- ◆ Future Technology Development Direction

Presentation Agenda

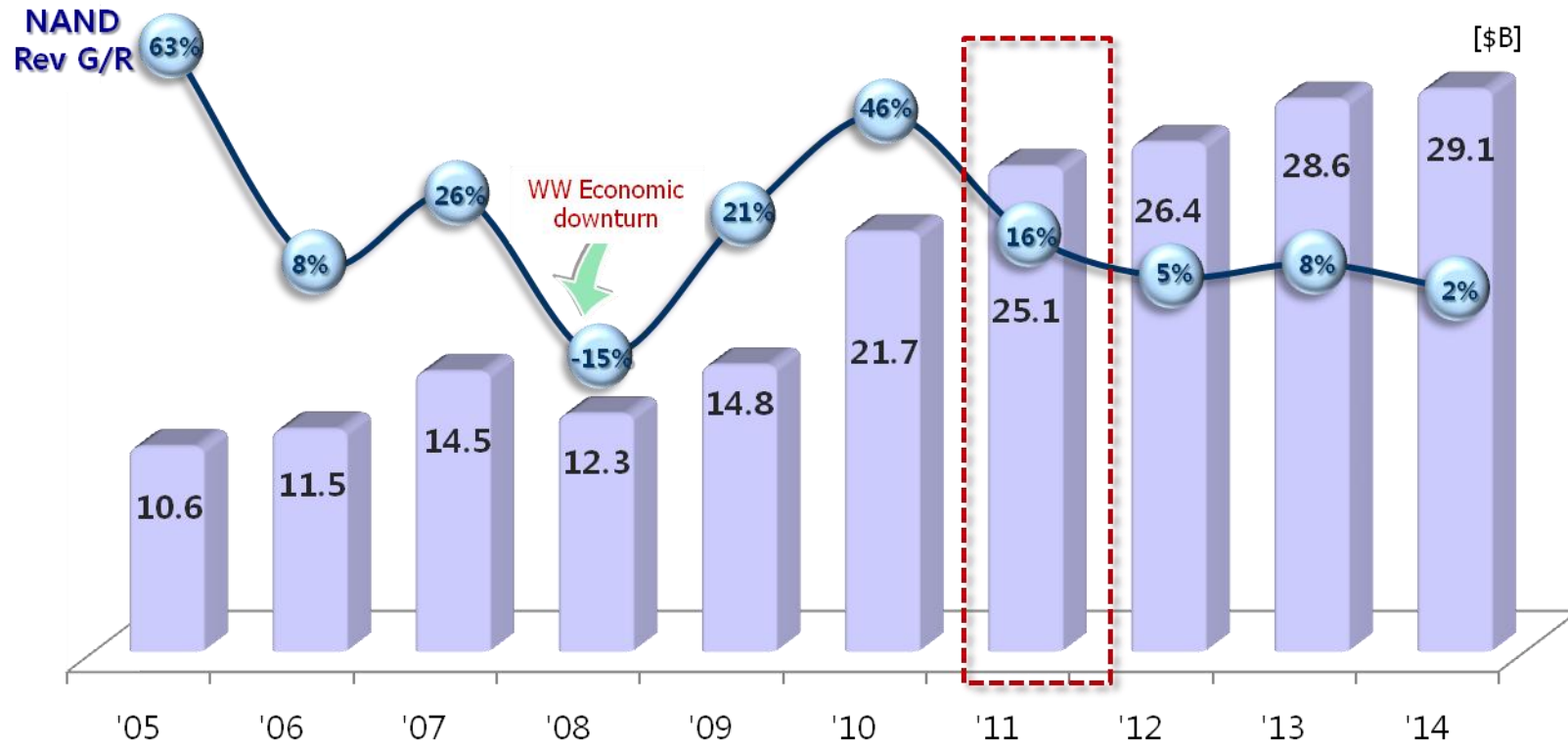
- ◆ **NAND Flash Market Overview**
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Market Revenue Forecasting

Expect continuous NAND market growth; \$29.1B in 2014

WW NAND Revenue Trend

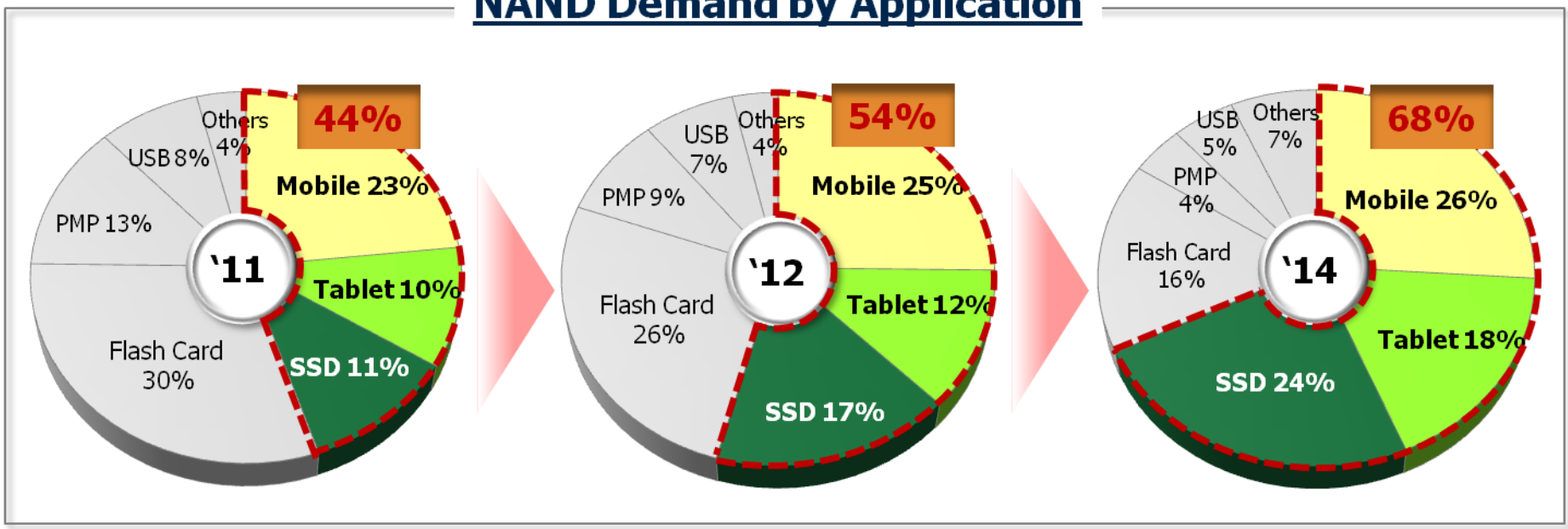


[Source; WSTS2011]

Prospective Application Trend

Mobile, Tablet, SSD dominate NAND demand in 2011~2014

NAND Demand by Application



[Source; Hynix Marketing 2011]

General Market Requirement

◆ Low Cost

✓ *Bit growth*

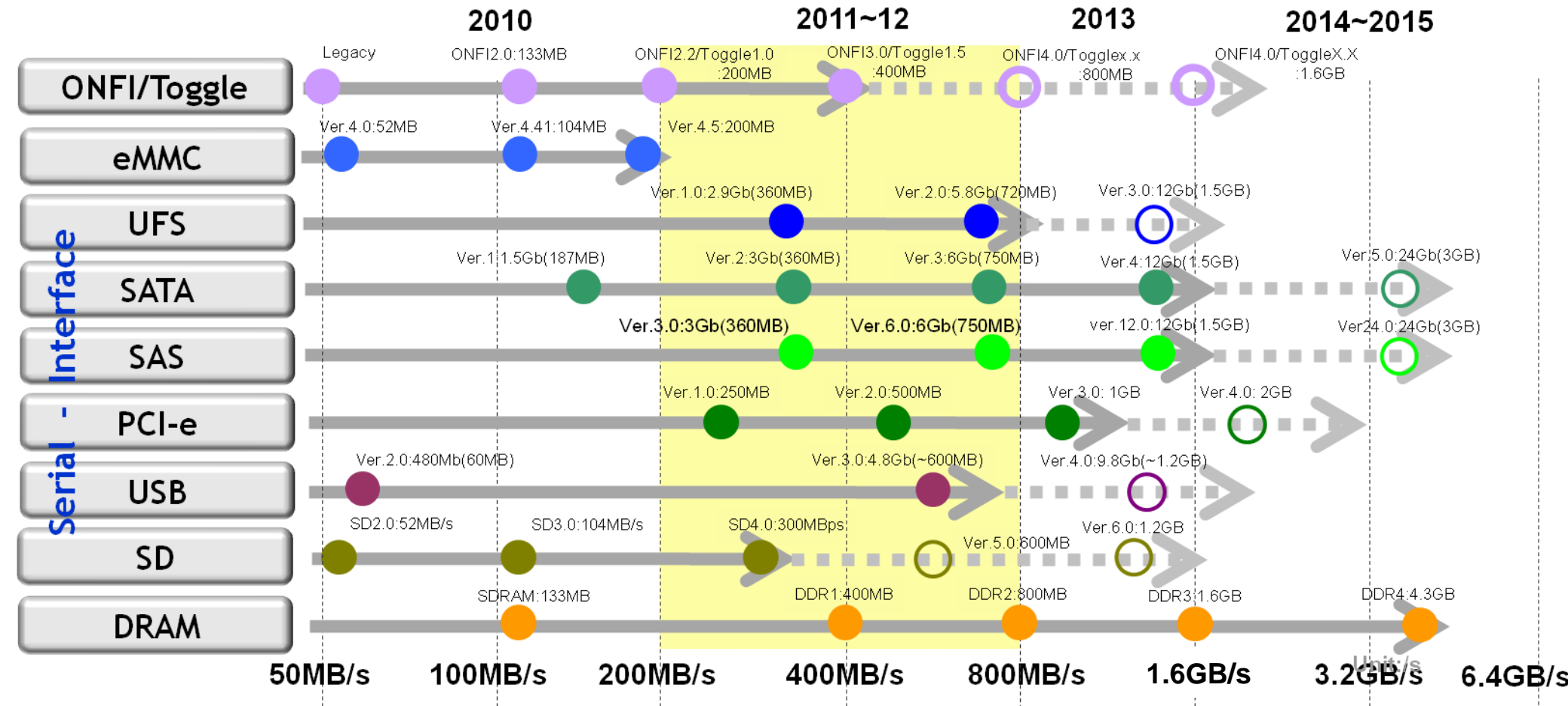
◆ High Performance

✓ + *Controller SW solution*

◆ High Reliability

✓ + *Controller SW solution*

Standard Interface Trend; *Performance*

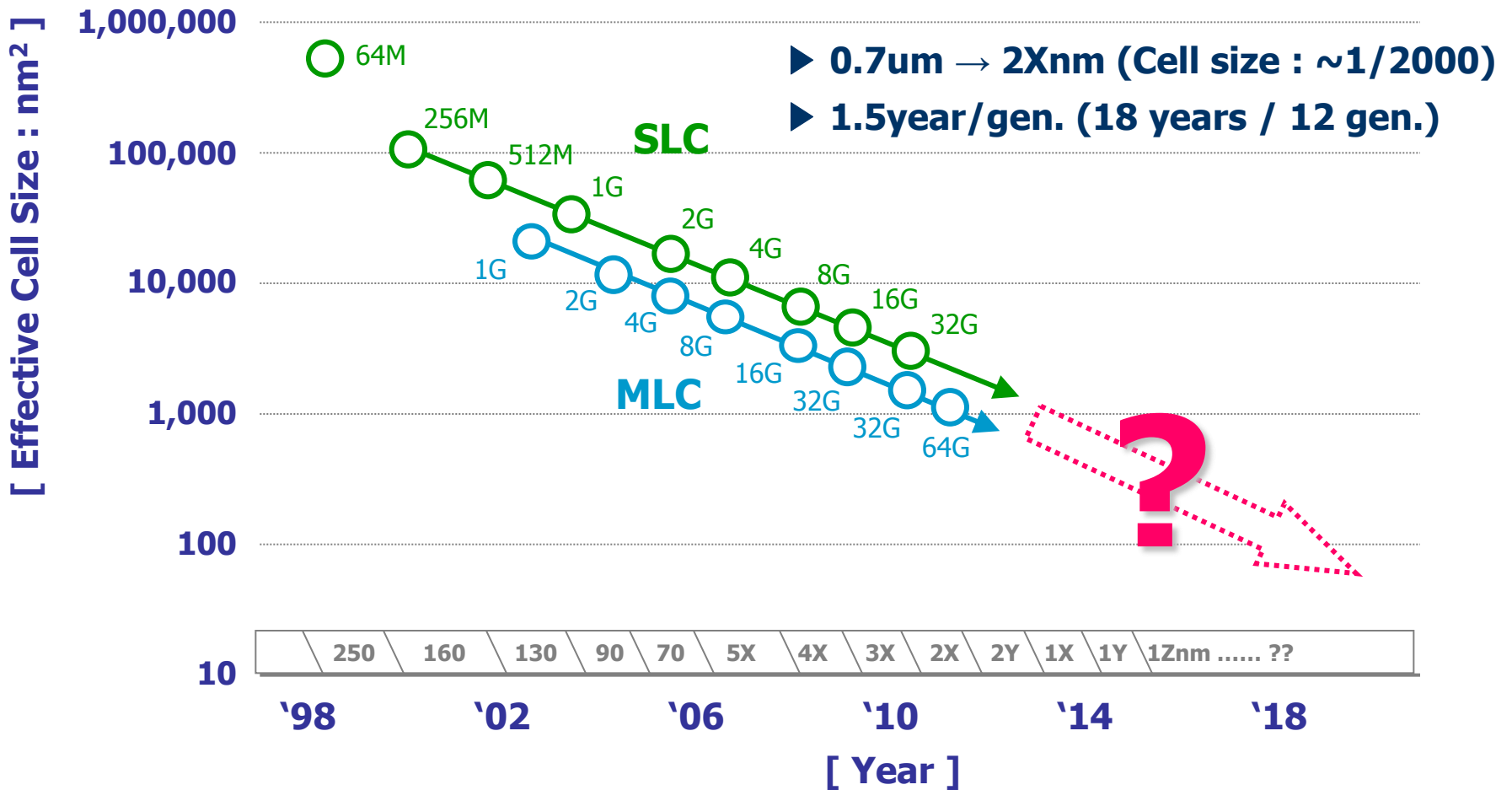


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Further Scaling Solution?

Conventional FG NAND cell has been scaled down over 18 years.





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Scaling Limitation of FG Cell

◆ Physical Limitation;

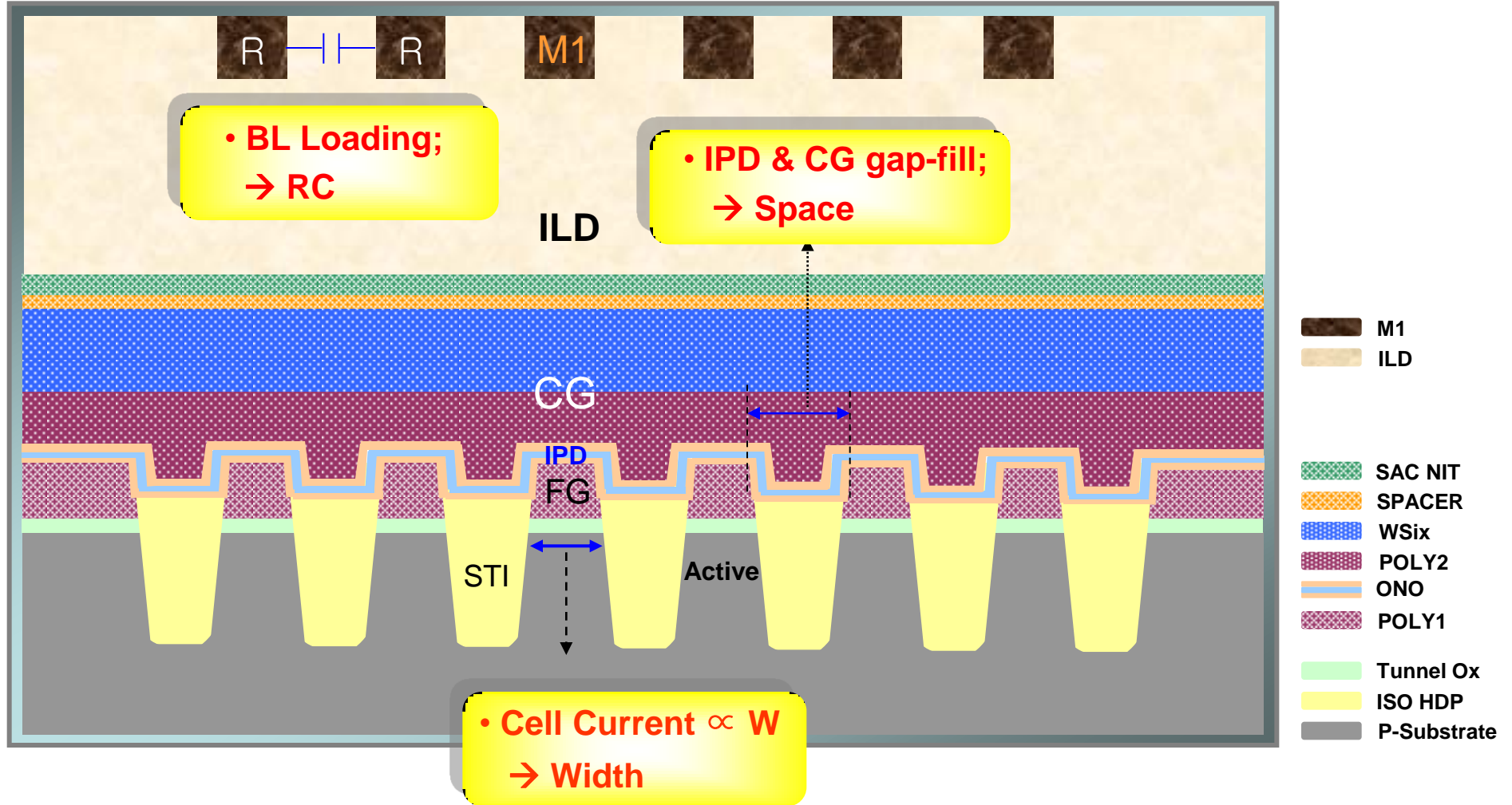
- ✓ *Patterning*
- ✓ *Structure formation : FG, CG, IPD ...*

◆ Electrical Limitation;

- ✓ *Interference*
- ✓ *Capacitive coupling ratio*
- ✓ *No. of electron in FG*
- ✓ *Dielectric leakage*

Cell Scaling Limitation; x-direction

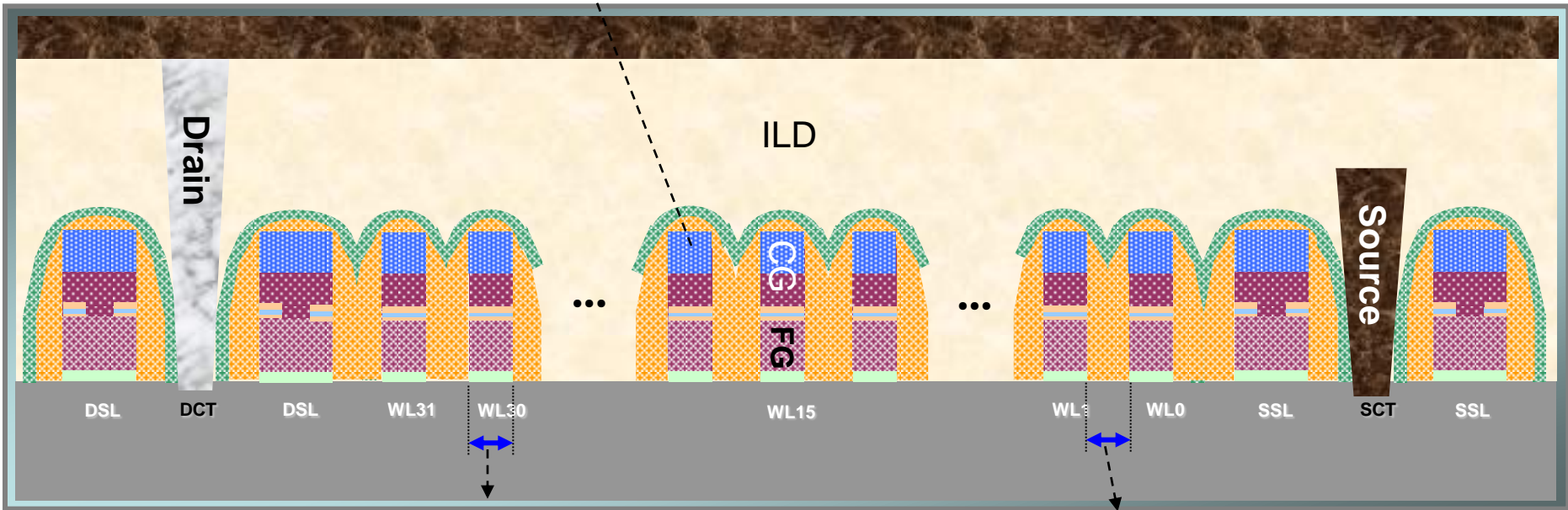
✓ **ASA-FG** Advanced Self-Aligned Floating Gate



Cell Scaling Limitation; y-direction

- M1
- ILD
- DCT
- SAC NIT
- SPACER
- WSix
- POLY2
- ONO
- POLY1
- Tunnel Ox

• WL Loading;
→ RC delay



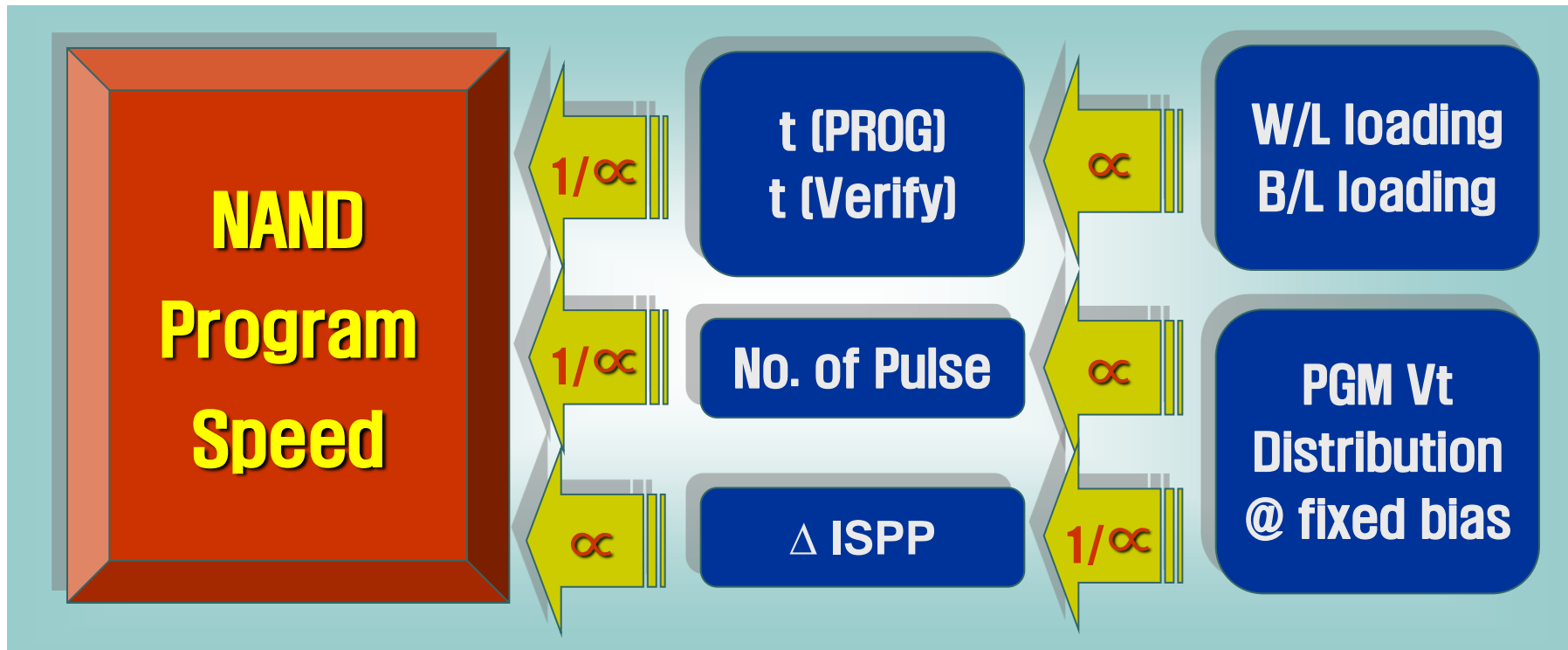
• Cell S/D Punch;
→ Off leakage

• Interference;
→ Vt distribution

NAND Program Speed

◆ Program Speed = $t \text{ (PROG + Verify)} \times N$

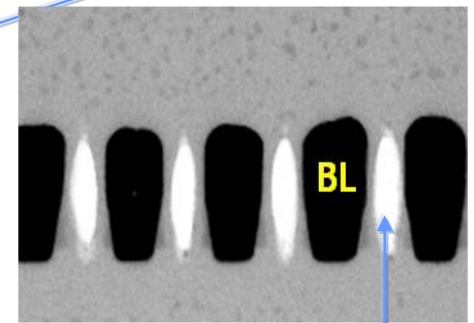
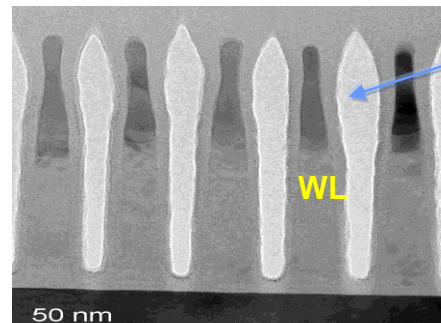
- t_{PROG} ; unit program & verify time
- N ; no. of ISPP



WL & BL Loading Improvement

◆ WL Loading

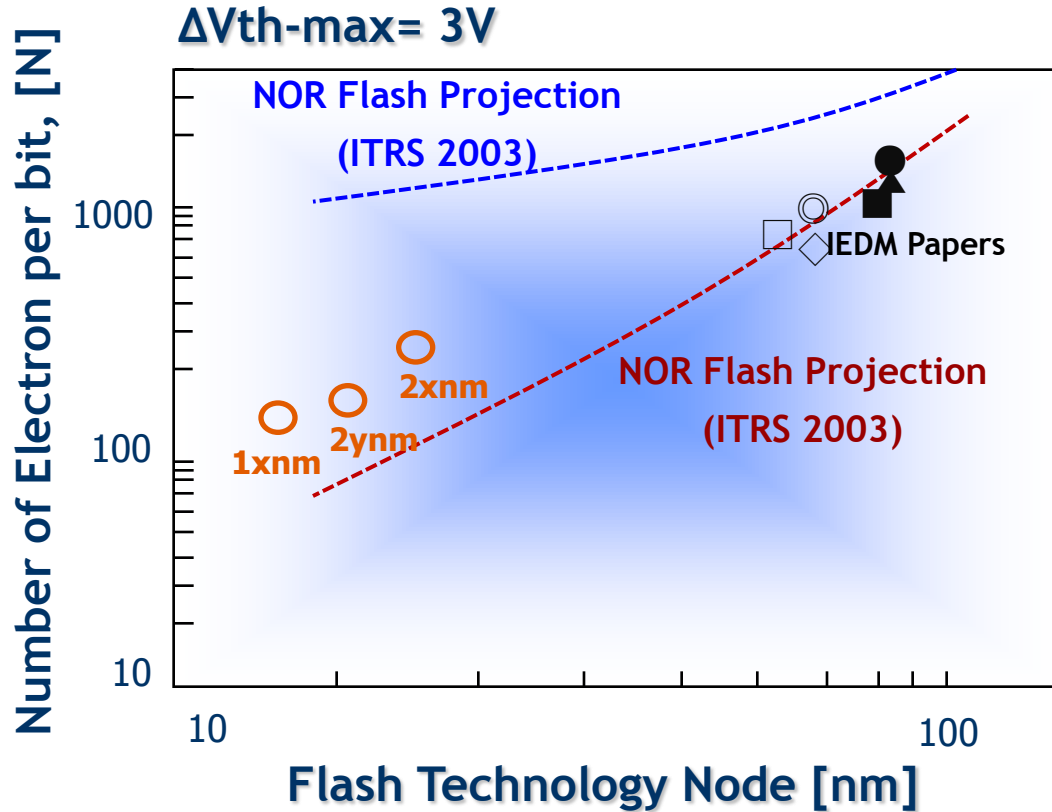
- *Material; Poly- Si → CoSix → W*
- *WL Space; Vertical Profile → Low-k dielectric → Air Gap*



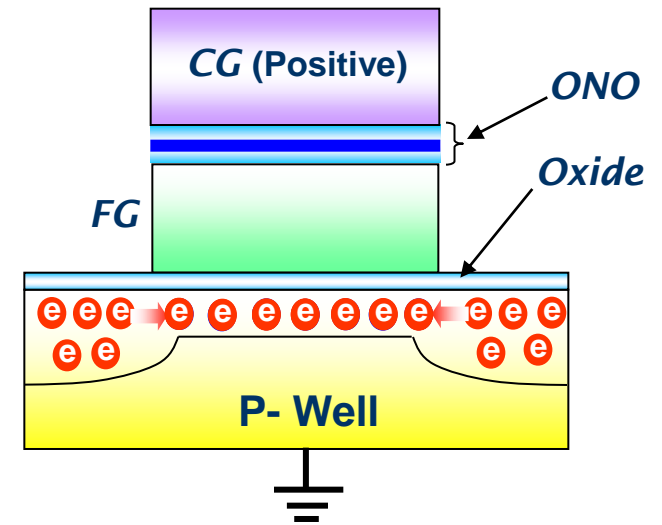
◆ BL Loading

- *Material; W → Al → Cu*
- *BL Space; Vertical Profile → Low-k dielectric → Air Gap*

No. of stored electrons in FG

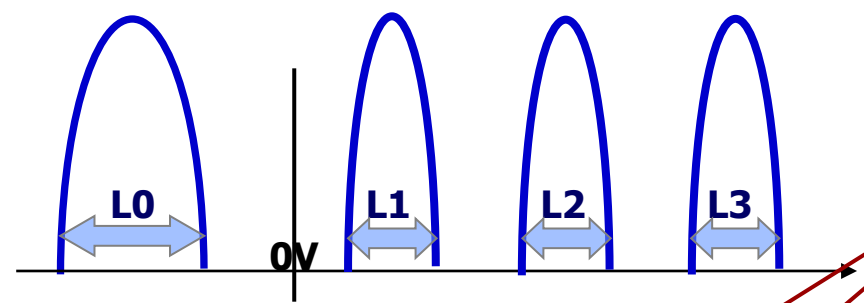


Program Operation



Read Window Margin Solution

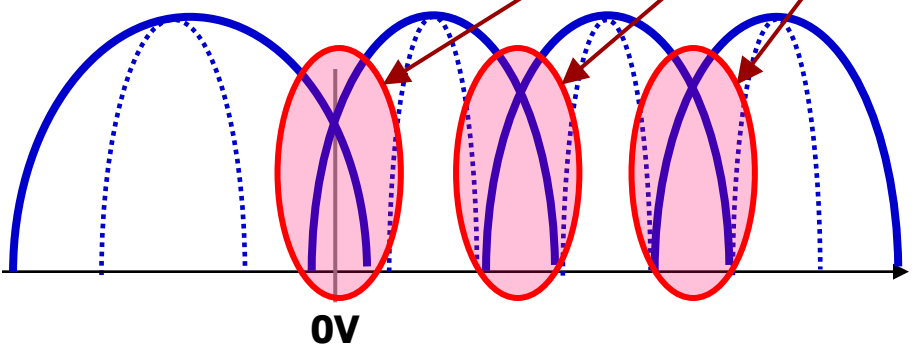
~2xnm



◆ Vt Distribution Overlap due to;

- ✓ *Process Variation*
- ✓ *Data Retention Shift*
- ✓ *FG-FG Interference*

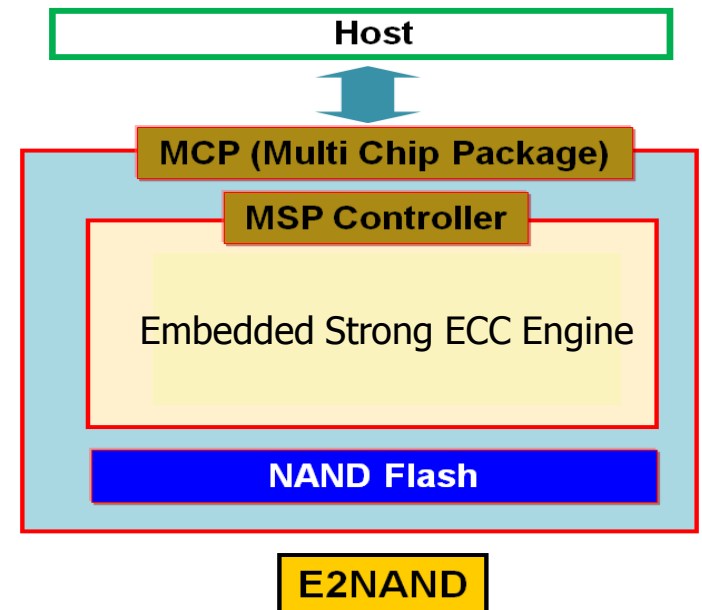
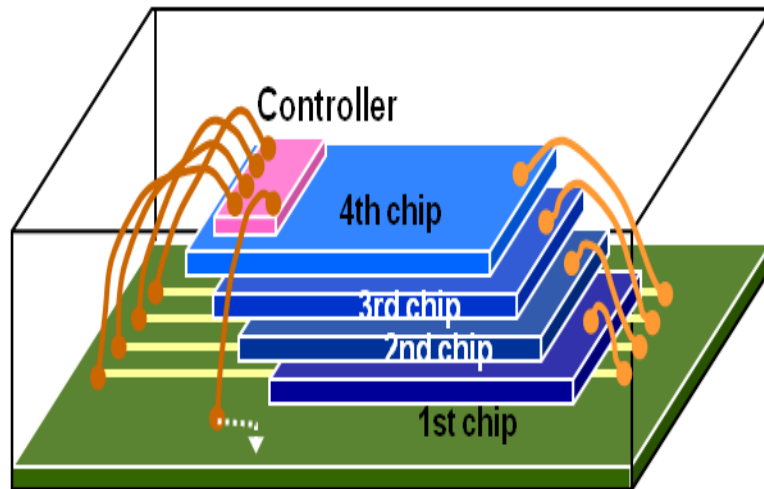
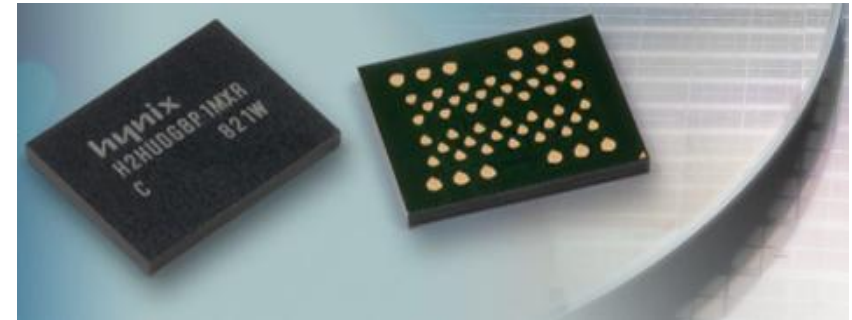
1xnm ~



- ◆ **Smart Read Algorithm**
- ◆ **Strong ECC**

Enhanced Solution Products

◆ Hynix; E2NAND [embedded-ECC]



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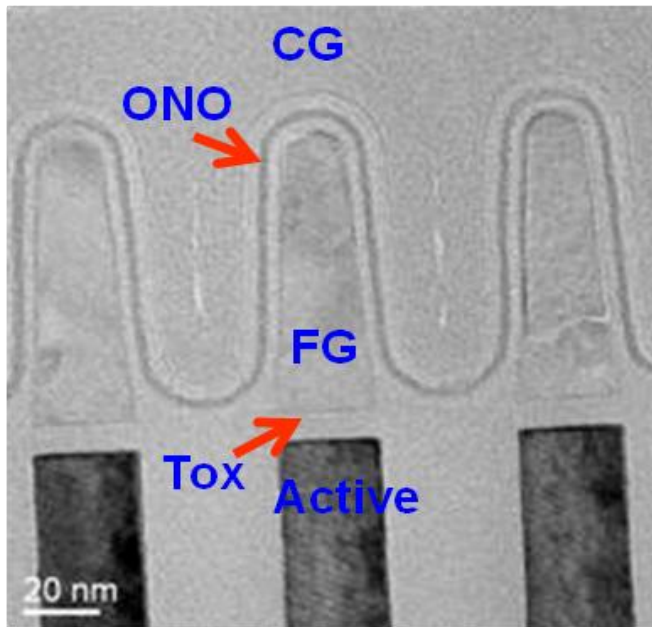
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Planar FG with High-k IPD

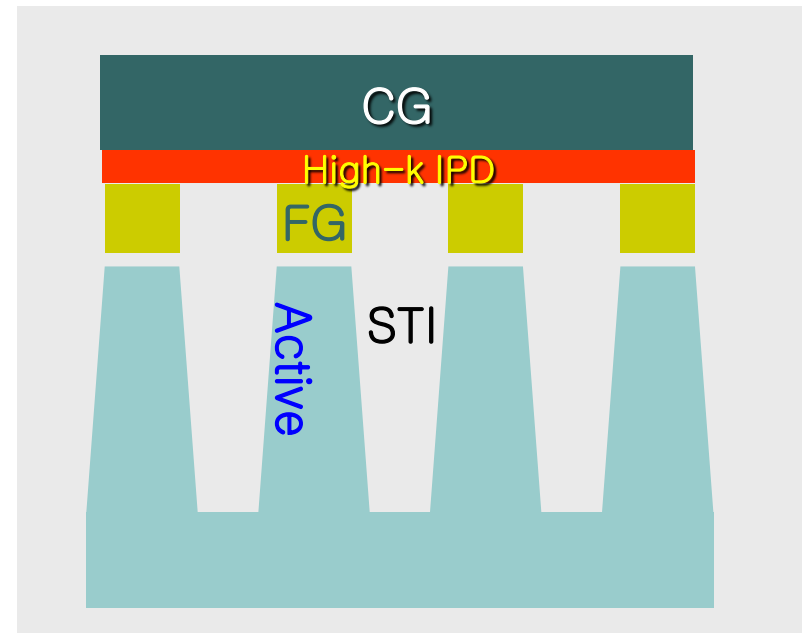
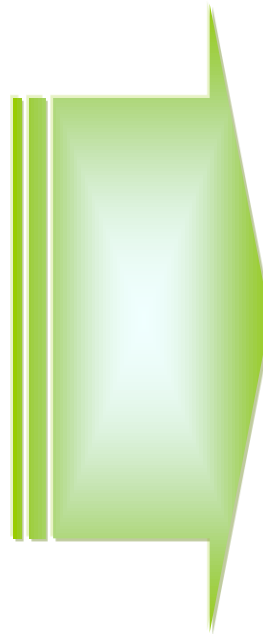
◆ CG Gap-filling & Interference

❖ Thin FG structure with High-k IPD

✓ *FG vertical scaling*



Conventional FG Structure



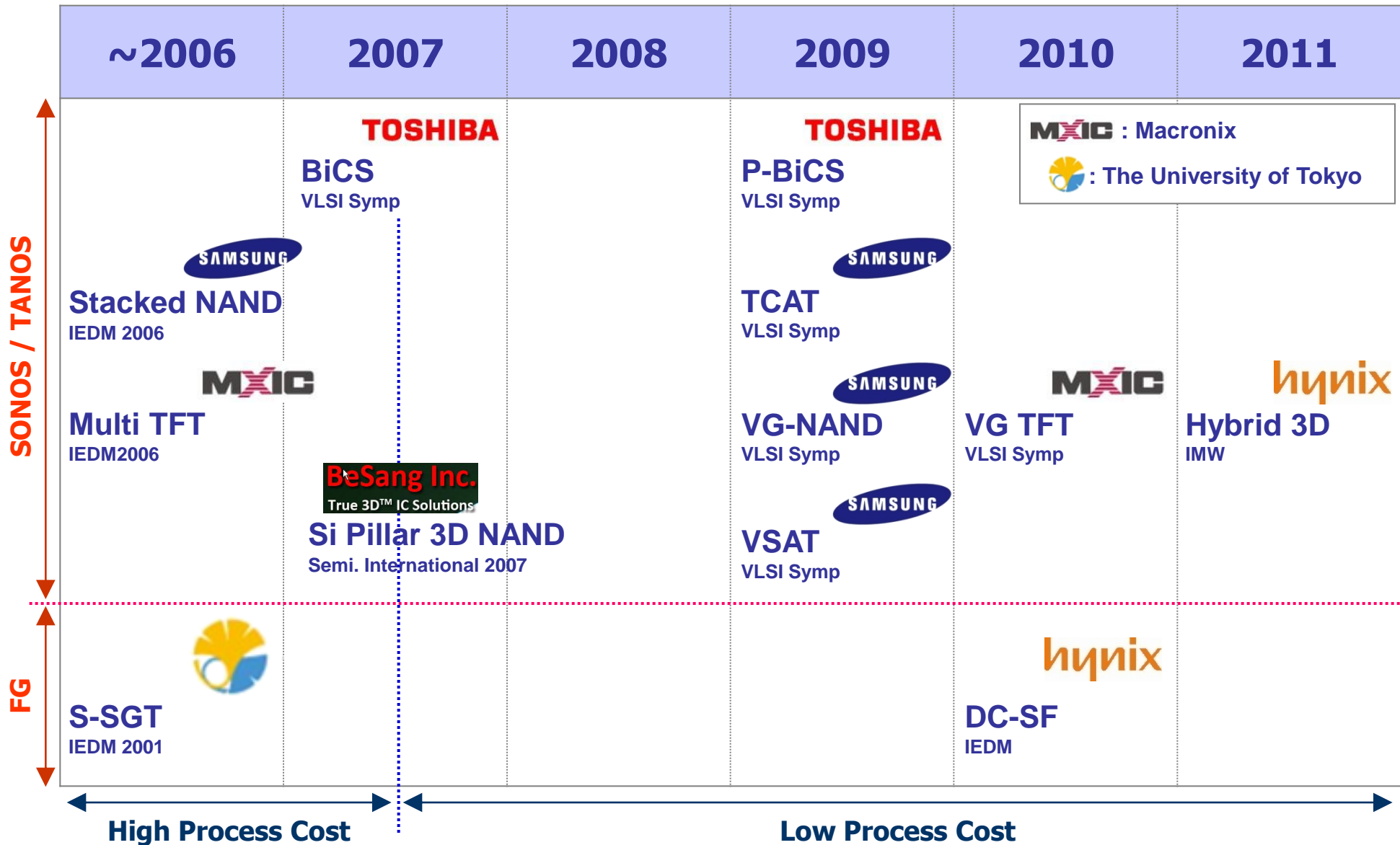
Planar FG Structure

3D Cell Structure Approach

- ◆ Stacked 3D with SONOS structure
- ◆ Stacked 3D with FG structure
- ◆ Si Pillar 3D with wafer bonding technology

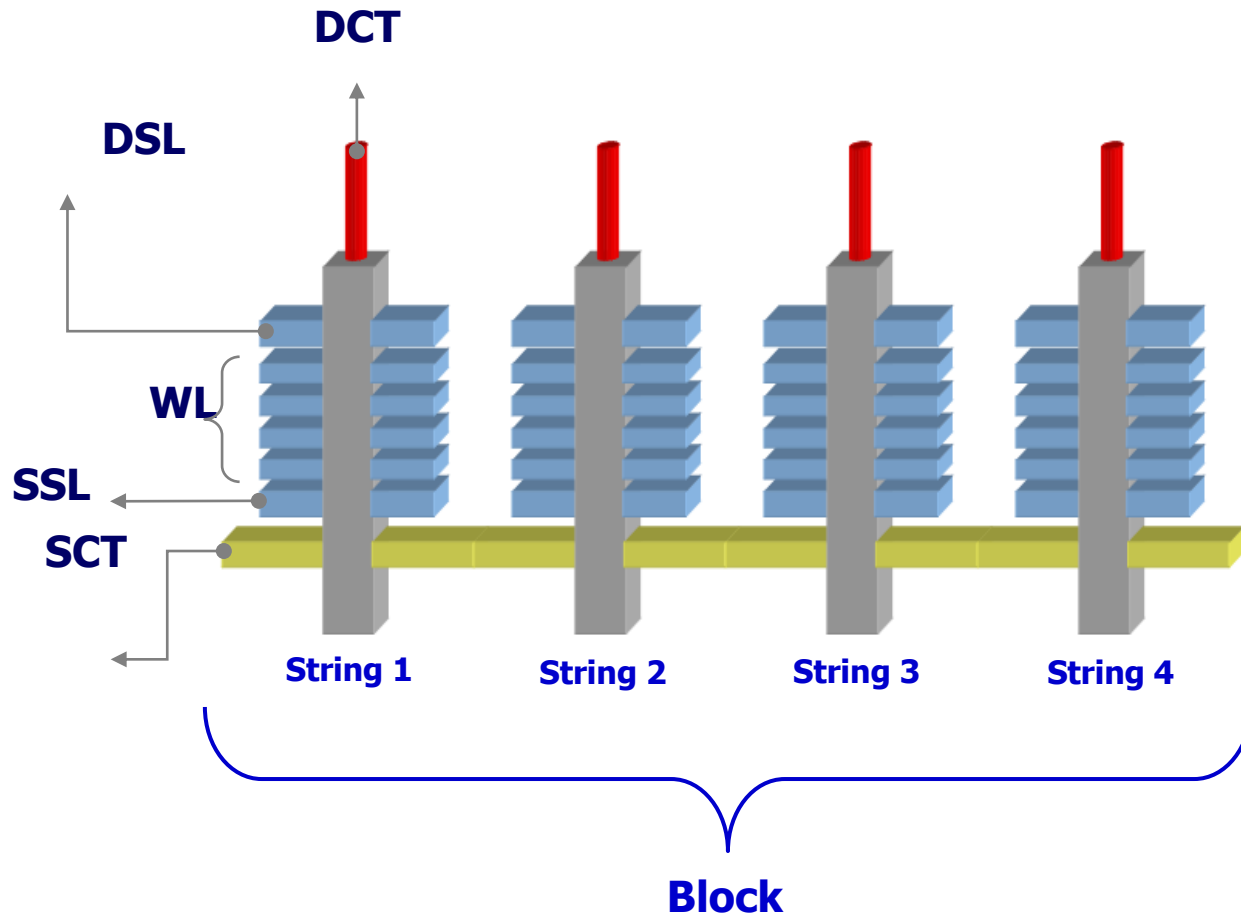


History of 3D NAND Flash



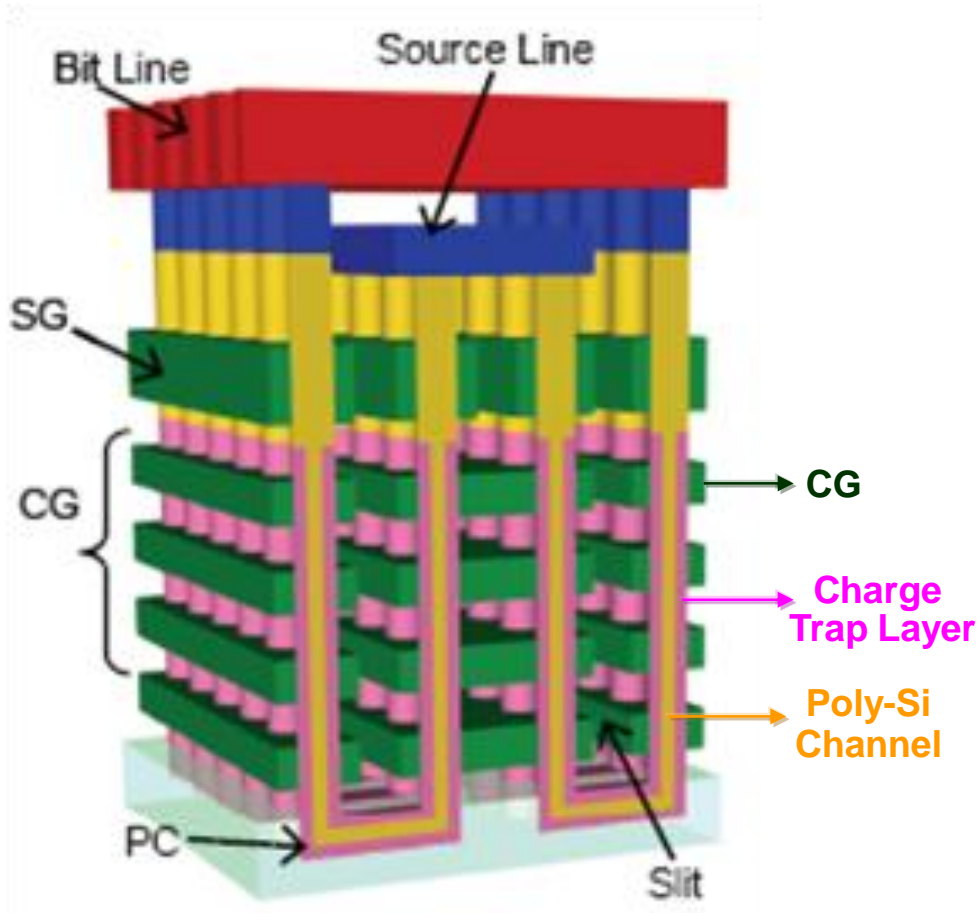
Stacked 3D NAND Flash Concept

3D NAND Cell string



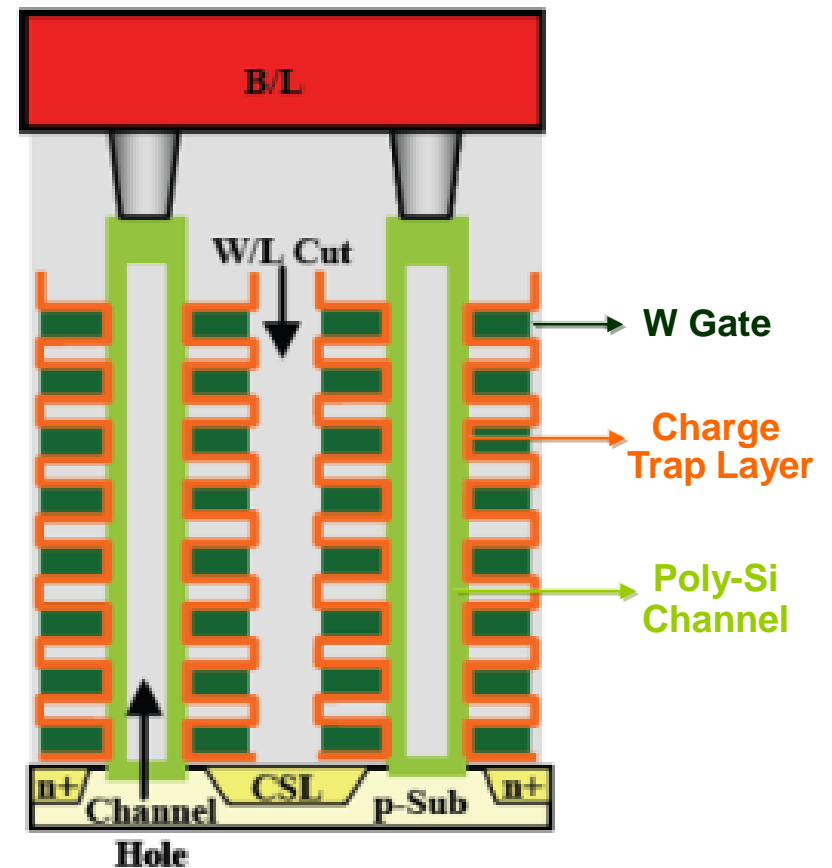
Stacked 3D Cell Structures

P-BiCS



[VLSI 2009 by Toshiba]

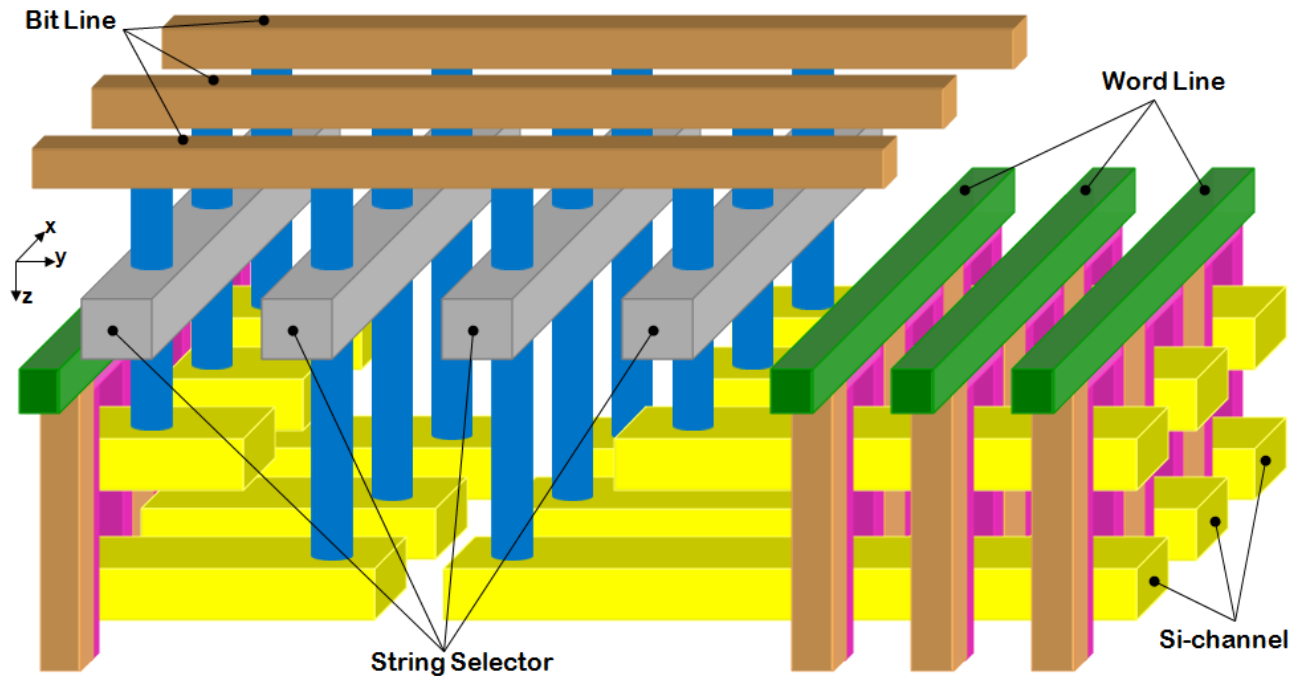
TCAT



[VLSI 2009 by Samsung]

Stacked 3D Cell Structures

Hybrid Stacked 3D



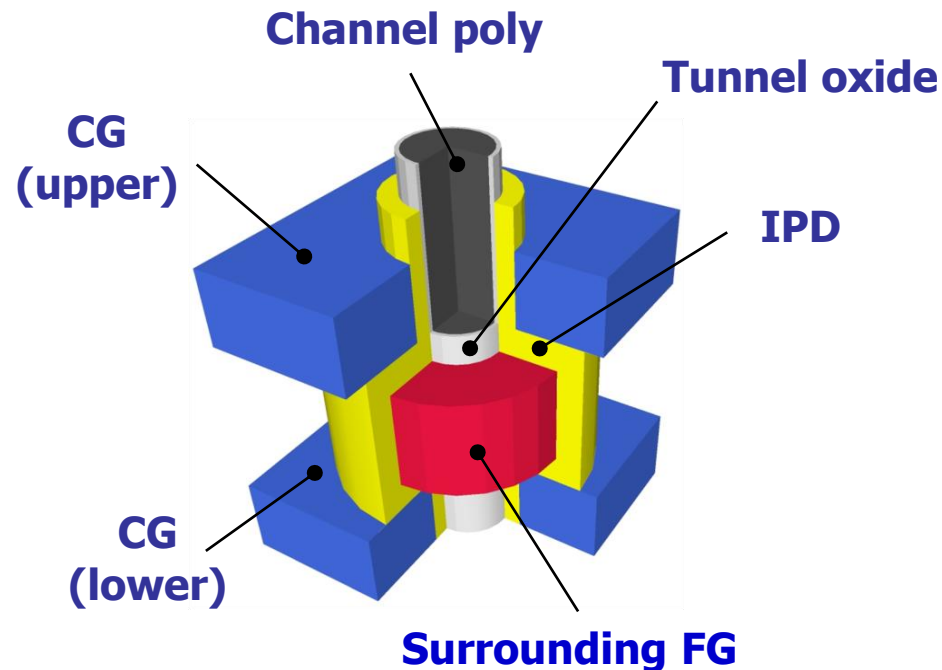
3D Cell Structure with Horizontal Poly-Si Channel

[IMW 2011 by Hynix]

Dual CG - Surrounding 3D FG Cell

- ◆ New 3D Structure Concept with **FG** cell
- ◆ Surrounding FG is controlled by two control gates.

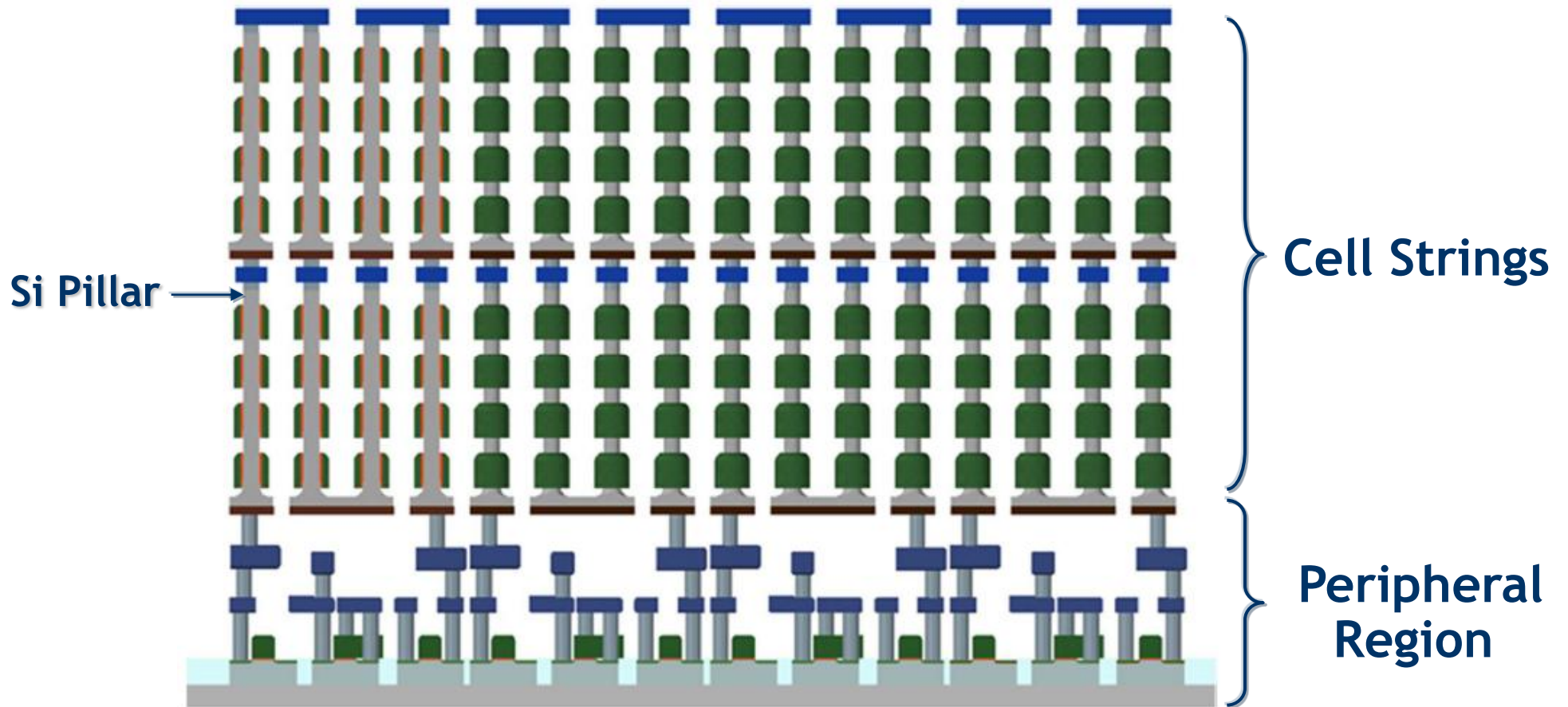
Single cell



*) Sung Jin Whang, et al, IEDM. 2010, pp.668-671

[IEDM 2010 by Hynix]

Si Pillar 3D Structure



[Semi. International 2007 by BeSang Tech.]

Future Technology Analysis

Technology	Strong Points	Weak Points
Planar FG	Friendly Structure	High-k Dielectric Stability
FG-3D	Reliability Small Interference	Scaling Limitation Stacking Limitation
Stacked 3D	Low Cost Small Interference	New Materials SONOS Reliability
Si Pillar	Approved Materials Scalability	Wafer Bonding Cost SONOS Reliability

What are Decision Points ?



Who is Winner at Post 1x or 1y nm ?



Somebody will find a solution.

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Thank you!